

**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****General Description**

The AH276 is an integrated Hall sensor with output driver designed for electronic commutation of brushless DC motor applications. The device includes an on-chip Hall sensor for magnetic sensing, an amplifier that amplifies the Hall voltage, a Schmitt trigger to provide switching hysteresis for noise rejection, a temperature compensation circuit to compensate the temperature drift of Hall sensitivity and two complementary open-collector drivers for sinking large load current. It also includes an internal band-gap regulator which is used to provide bias voltage for internal circuits.

Placing the device in a variable magnetic field, if the magnetic flux density is larger than threshold B_{OP} , the pin DO will be turned low (on) and pin DOB will be turned high (off). This output state is held until the magnetic flux density reverses and falls below B_{RP} , then causes DO to be turned high (off) and DOB turned low (on).

AH276 is available in TO-94 (SIP-4L) package.

Features

- On-Chip Hall Sensor
- 3.5V to 16V Supply Voltage
- 350mA (avg) Output Sink Current
- Reversed Supply Voltage Protection
- Build in Over Temperature Protection Function
- -20°C to 85°C Operating Temperature
- Low Profile TO-94 (SIP-4L) Package
- ESD Rating: 300V (Machine Model)

Applications

- Dual-Coil Brushless DC Motor
- Dual-Coil Brushless DC Fan
- Revolution Counting
- Speed Measurement

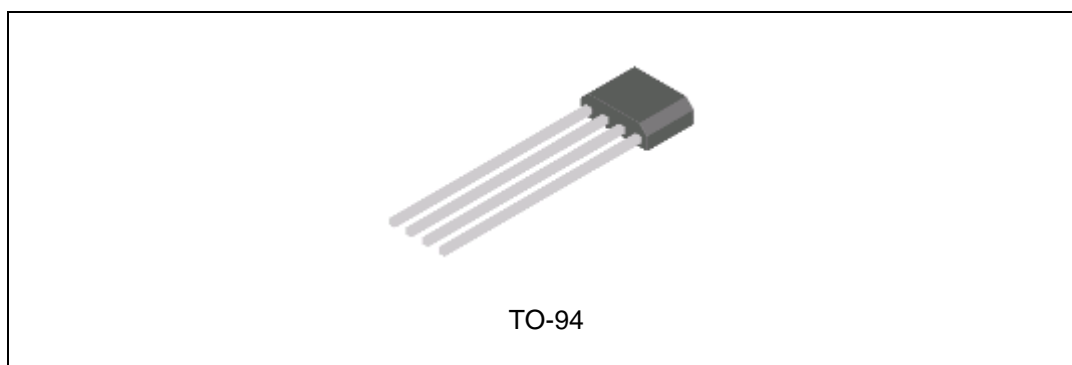


Figure 1. Package Type of AH276

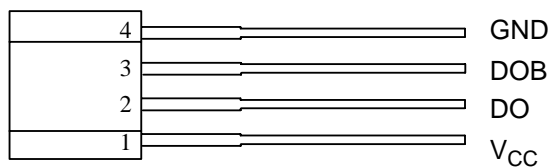
**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****Pin Configuration**Z4 Package
(TO-94)

Figure 2. Pin Configuration of AH276 (Front View)

Pin Description

| Pin Number | Pin Name | Function |
|------------|-----------------|----------------|
| 1 | V _{CC} | Supply voltage |
| 2 | DO | Output 1 |
| 3 | DOB | Output 2 |
| 4 | GND | Ground |



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Functional Block Diagram

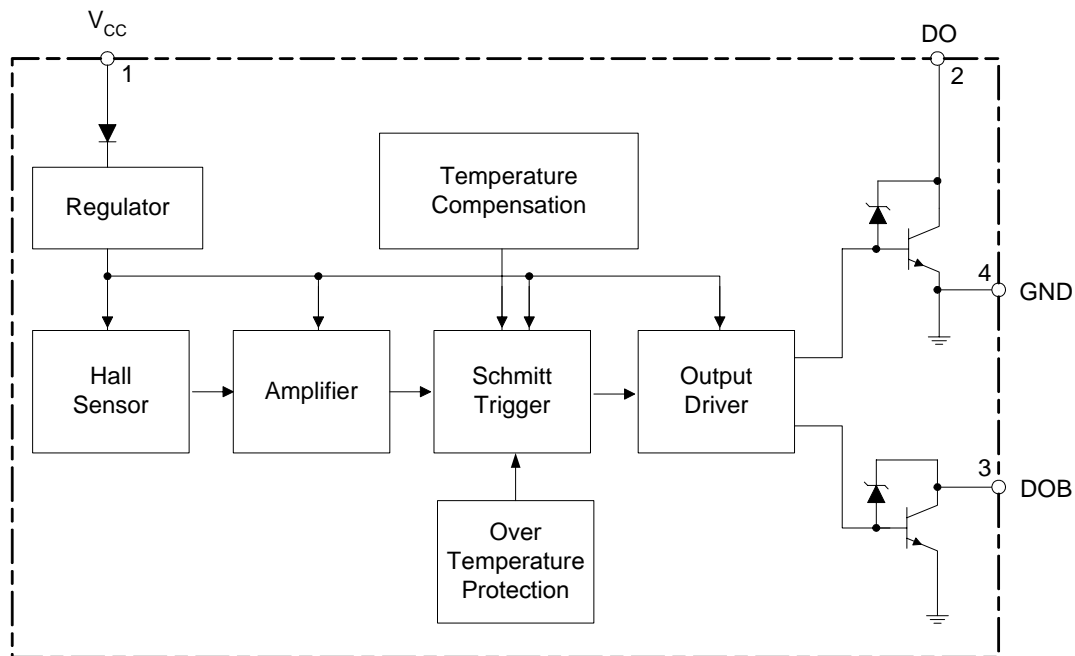
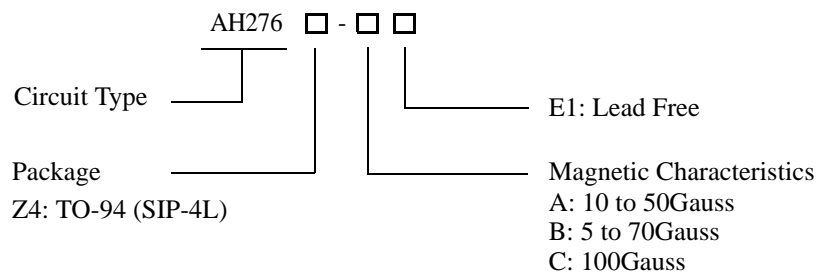


Figure 3. Functional Block Diagram of AH276

Ordering Information



| Package | Temperature Range | Part Number | Marking ID | Packing Type |
|---------|-------------------|-------------|------------|--------------|
| TO-94 | -20 to 85 °C | AH276Z4-AE1 | AH276Z4-E1 | Bulk |
| | | AH276Z4-BE1 | AH276Z4-E1 | Bulk |
| | | AH276Z4-CE1 | AH276Z4-E1 | Bulk |

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant.

**COMPLEMENTARY OUTPUT HALL EFFECT LATCH****AH276****Absolute Maximum Ratings (Note 1)** $(T_A=25^{\circ}\text{C})$

| Parameter | Symbol | Value | Unit |
|----------------------------|---------------------|---------------|------------------------------------|
| Supply Voltage | V_{CC} | 20 | V |
| Reverse Protection Voltage | V_{RCC} | -20 | V |
| Magnetic Flux Density | B | Unlimited | Gauss |
| Output Current | Continuous | 350 | mA |
| | Hold | 550 | mA |
| | Peak (start up) | 750 | mA |
| Power Dissipation | P_D | 550 | mW |
| Thermal Resistance | Die to atmosphere | θ_{JA} | 227 $^{\circ}\text{C}/\text{W}$ |
| | Die to package case | θ_{JC} | 49 $^{\circ}\text{C}/\text{W}$ |
| Storage Temperature | T_{STG} | -50 to 150 | $^{\circ}\text{C}$ |
| ESD (Machine Model) | | 300 | V |
| ESD (Human Body Model) | | 2500 | V |

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. "Absolute Maximum Ratings" for extended period may affect device reliability.

Recommended Operating Conditions $(T_A=25^{\circ}\text{C})$

| Parameter | Symbol | Min | Max | Unit |
|---------------------|----------|-----|-----|--------------------|
| Supply Voltage | V_{CC} | 3.5 | 16 | V |
| Ambient Temperature | T_A | -20 | 85 | $^{\circ}\text{C}$ |



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Electrical Characteristics

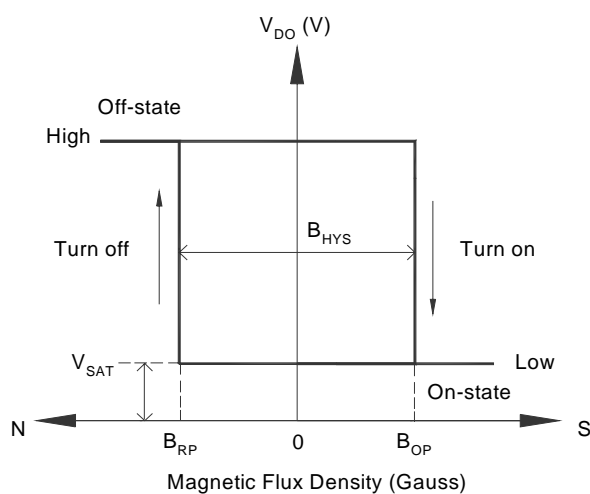
($T_A=25^{\circ}\text{C}$, $V_{CC}=14\text{V}$, unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|--------------------------------|--------------------|---|-----|------|-----|--------------------|
| Output Saturation Voltage | V_{SAT} | $V_{CC}=3.5\text{V}$, $I_O=100\text{mA}$ | | 0.3 | | V |
| | | $I_O=350\text{mA}$ | | 0.35 | 0.6 | V |
| Output Leakage Current | I_{OL} | $V_{CE}=16\text{V}$ | | 0.1 | 10 | μA |
| Supply Current | I_{CC} | $V_{CC}=16\text{V}$, Output Open | | 12 | 16 | mA |
| Output Rise Time | t_r | $R_L=820\Omega$, $C_L=20\text{pF}$ | | 3.0 | 10 | μs |
| Output Fall Time | t_f | $R_L=820\Omega$, $C_L=20\text{pF}$ | | 0.3 | 1.5 | μs |
| Switch Time Differential | Δt | $R_L=820\Omega$, $C_L=20\text{pF}$ | | 3.0 | 10 | μs |
| Output Zener Breakdown Voltage | V_Z | | | 55 | | V |
| Thermal Protection Temperature | TSD | | | 178 | | $^{\circ}\text{C}$ |
| Thermal Protection Hysteresis | ΔTSD | | | 40 | | $^{\circ}\text{C}$ |

Magnetic Characteristics

($T_A=25^{\circ}\text{C}$)

| Parameter | Symbol | Grade | Min | Typ | Max | Unit |
|-----------------|-----------|-------|------|-----|-----|-------|
| Operating Point | B_{OP} | A | 10 | | 50 | Gauss |
| | | B | 5 | | 70 | Gauss |
| | | C | | | 100 | Gauss |
| Releasing Point | B_{RP} | A | -50 | | -10 | Gauss |
| | | B | -70 | | -5 | Gauss |
| | | C | -100 | | | Gauss |
| Hysteresis | B_{HYS} | | | 75 | | Gauss |





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Magnetic Characteristics (Continued)

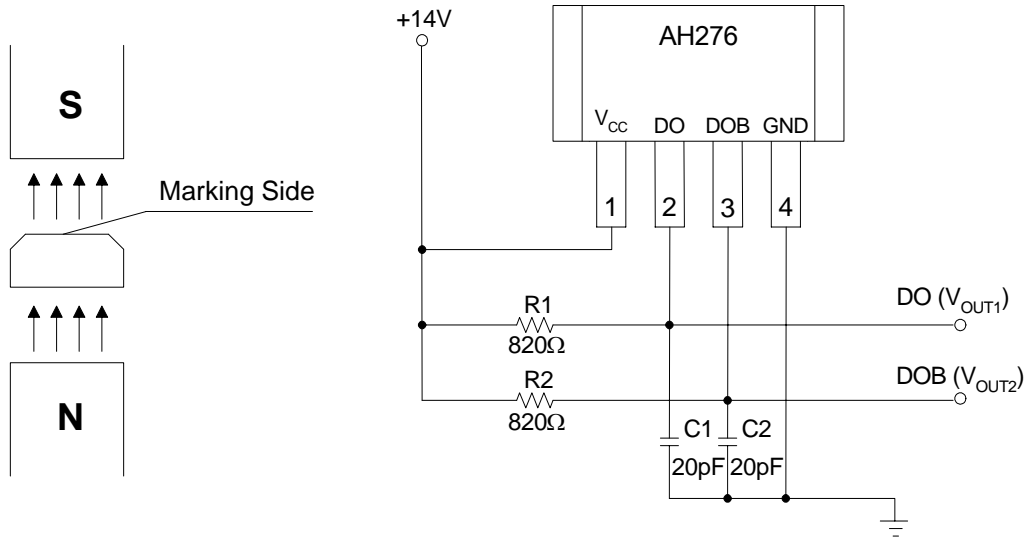


Figure 4. Basic Test Circuit

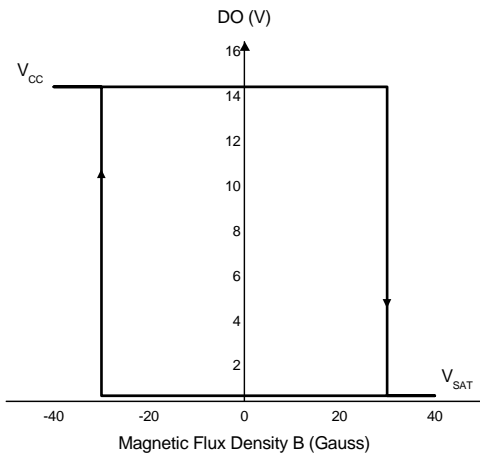


Figure 5. V_{DO} vs. Magnetic Flux Density

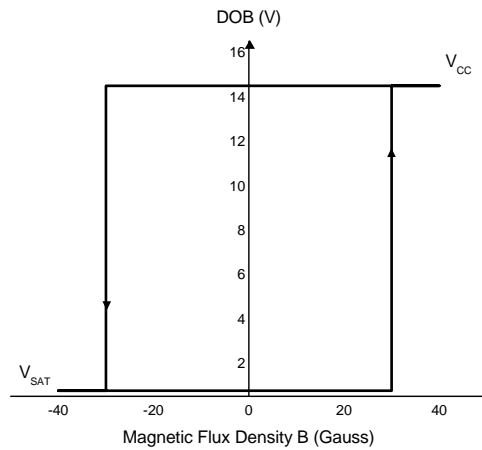


Figure 6. V_{DOB} vs. Magnetic Flux Density



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Typical Performance Characteristics

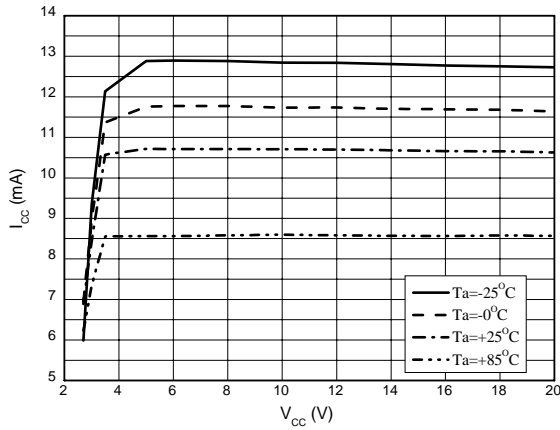


Figure 7. I_{CC} vs. V_{CC}

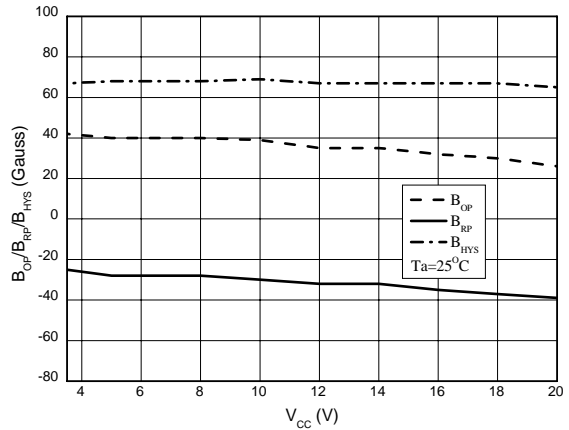


Figure 8. $B_{OP}/B_{RP}/B_{HYS}$ vs. V_{CC}

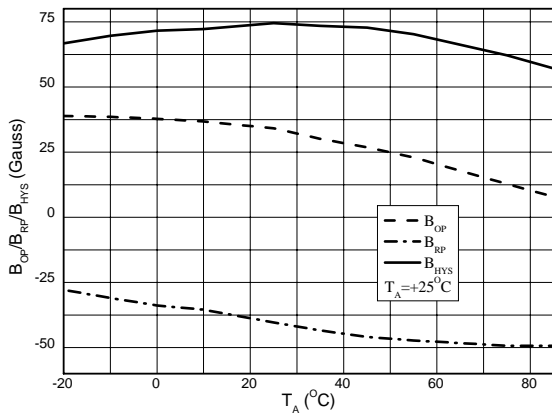


Figure 9. $B_{OP}/B_{RP}/B_{HYS}$ vs. Ambient Temperature

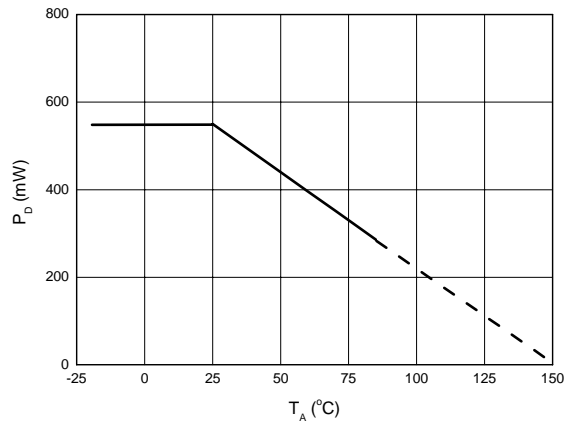


Figure 10. P_D vs. Ambient Temperature



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Typical Performance Characteristics (Continued)

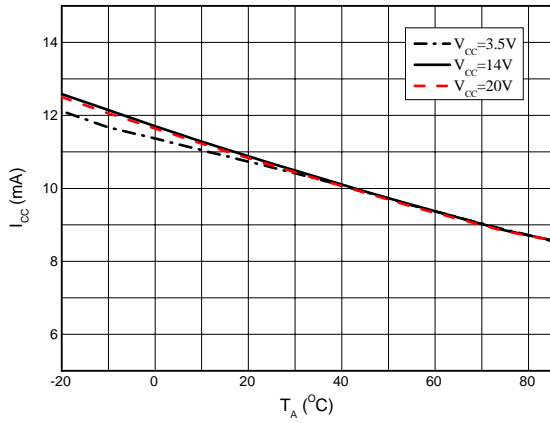


Figure 11. I_{CC} vs. Ambient Temperature

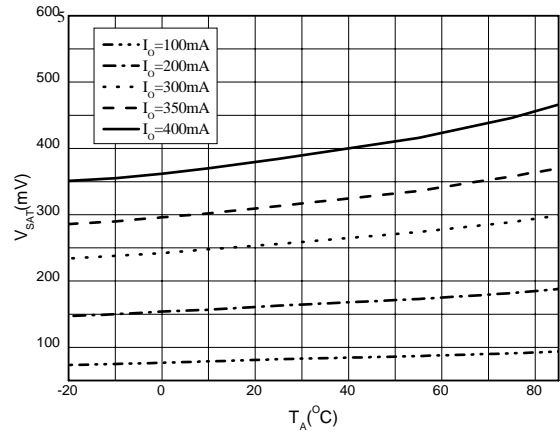


Figure 12. V_{SAT} vs. Ambient Temperature

Typical Applications

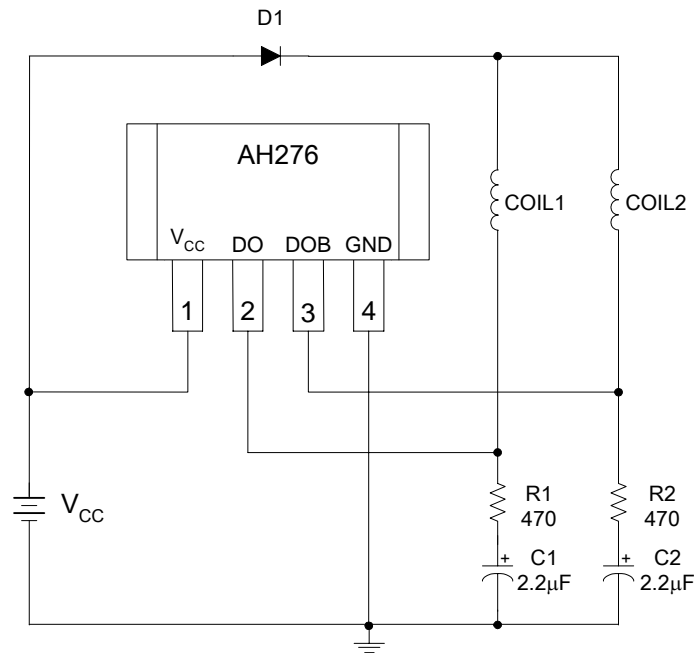


Figure 12. Typical Application Circuit



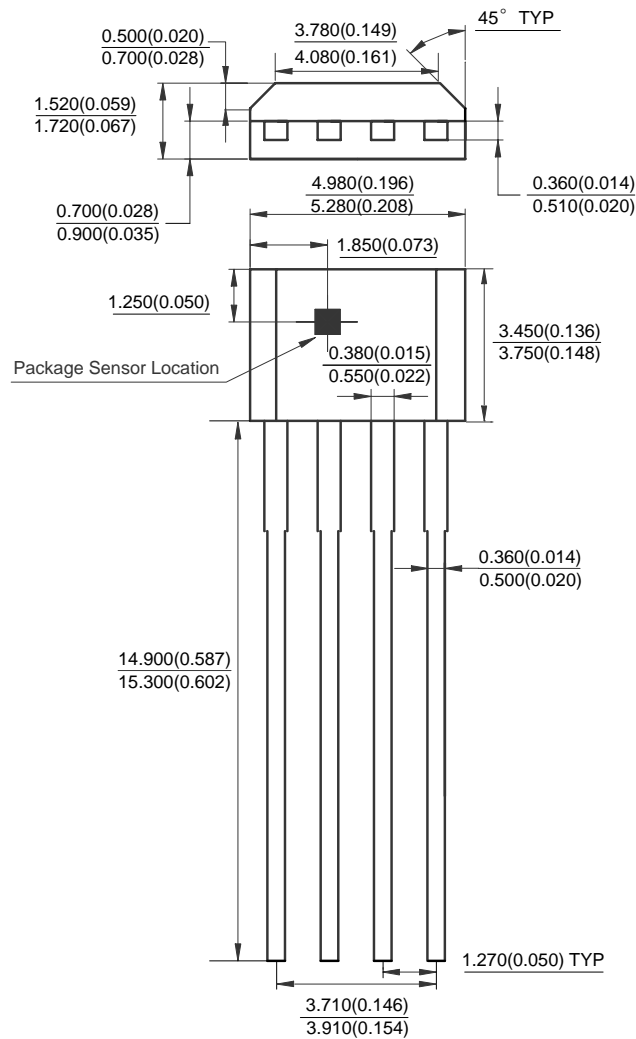
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Mechanical Dimensions

TO-94

Unit: mm(inch)





BCD Semiconductor Manufacturing Limited

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